

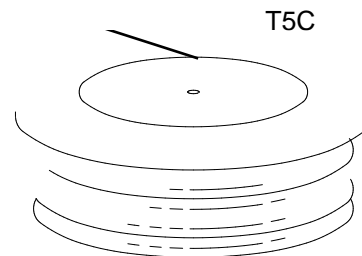
KK640-FAST SWITCHING THYRISTOR

1200-1400 V_{DRM}

HIGH POWER THYRISTOR FOR INVERTER APPLICATION

Features:

- . All Diffused Structure
- . Amplifying Gate Configuration
- . Blocking capability up to 1400 volts
- . High dv/dt Capability
- . Pressure Assembled Device



ELECTRICAL CHARACTERISTICS AND RATINGS

Blocking - Off State

Device Type	V_{RRM} (1)	V_{DRM} (1)	V_{RSM} (1)
KK640/12	1200	1200	1400
KK640/14	1400	1400	1600

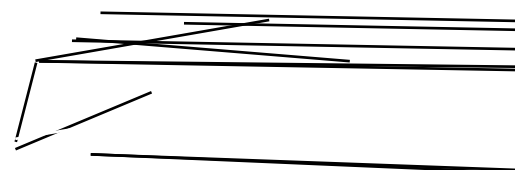
V_{RRM} = Repetitive peak reverse voltage

V_{DRM} = Repetitive peak off state voltage

V_{RSM} = Non repetitive peak reverse voltage (2)

Repetitive peak reverse leakage and off state leakage	I_{RRM}/I_{DRM}	2 mA 20 mA (3)
Critical rate of voltage rise	dv/dt (4)	1000 V/ μ s

Conducting - On State



ELECTRICAL CHARACTERISTICS AND RATINGS KK640-FAST SWITCHING THYRISTOR

Gating

Parameter	Symbol	Min.	Max.	Typ.	Units	Conditions
Peak gate power dissipation	P_{GM}		20		W	
Average gate power dissipation	$P_{G(AV)}$		4		W	
Gate-trigger current	I_{GT}		150		mA	$V_D=12V; R_L=3ohms; T_j=+25^{\circ}C$
Gate- trigger voltage	V_{GT}	0.70	2.5		V	$V_{\mu R}$



